



N-Channel NexFET[™] Power MOSFETs

Check for Samples: CSD16323Q3

FEATURES

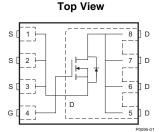
- **Optimized for 5V Gate Drive**
- Ultra Low Qg and Qgd
- Low Thermal Resistance
- **Avalanche Rated**
- **Pb Free Terminal Plating**
- **RoHS Compliant**
- **Halogen Free**
- SON 3.3mm x 3.3mm Plastic Package

APPLICATIONS

- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and **Computing Systems**
- **Optimized for Control or Synchronous FET** Applications

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion and optimized for 5V gate drive applications.



PRODUCT SUMMARY

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V _{DS}	Drain to Source Voltage	25		V
Qg	Gate Charge Total (4.5V)	6.2		nC
Q _{gd}	Gate Charge Gate to Drain	1.1		nC
		$V_{GS} = 3V$	5.4	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V$	4.4	mΩ
		$V_{GS} = 8V$	3.8	mΩ
V _{th}	Threshold Voltage	1.1		V

ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD16323Q3	SON 3.3 × 3.3 Plastic Package	13-inch reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

$T_A = 2$	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	+10 /8	V
	Continuous Drain Current, T _C = 25°C	60	А
ID	Continuous Drain Current ⁽¹⁾	21	А
I _{DM}	Pulsed Drain Current, $T_A = 25^{\circ}C^{(2)}$	112	А
PD	Power Dissipation ⁽¹⁾	3	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, single pulse $I_D = 50A$, L = 0.1mH, $R_G = 25\Omega$	125	mJ

(1) $R_{\theta JA} = 43^{\circ}C/W$ on $1in^2$ Cu (2 oz.) on 0.060" thick FR4 PCB.

(2) Pulse width ≤300µs, duty cycle ≤2%



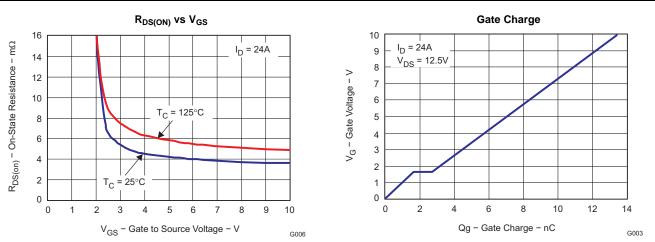
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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Cl	haracteristics					
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25			V
I _{DSS}	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 20V$			1	μA
I _{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +10/-8V$			100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.9	1.1	1.4	V
R _{DS(on)}		$V_{GS} = 3V, I_D = 24A$		5.4	7.2	mΩ
	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 24A$		4.4	5.5	mΩ
		$V_{GS} = 8V, I_D = 24A$		3.8	4.5	mΩ
9 _{fs}	Transconductance $V_{DS} = 12.5V, I_D = 24A$			108		S
Dynamic	Characteristics	· · · · · · · · · · · · · · · · · · ·				
C _{ISS}	Input Capacitance			1020	1300	pF
C _{OSS}	Output Capacitance	V _{GS} = 0V, V _{DS} = 12.5V, f = 1MHz		740	960	pF
C _{RSS}	Reverse Transfer Capacitance			50	65	pF
R _g	Series Gate Resistance			1.4	2.8	Ω
Qg	Gate Charge Total (4.5V)			6.2	8.4	nC
Q _{gd}	Gate Charge Gate to Drain			1.1		nC
Q _{gs}	Gate Charge Gate to Source	V _{DS} = 12.5V, I _D = 24A		1.8		nC
Qg(th)	Gate Charge at Vth			1		nC
Q _{OSS}	Output Charge	$V_{DS} = 12.5V, V_{GS} = 0V$		14		nC
t _{d(on)}	Turn On Delay Time			5.3		ns
t _r	Rise Time	V _{DS} = 12.5V, V _{GS} = 4.5V I _D = 24A		15		ns
t _{d(off)}	Turn Off Delay Time	$R_G = 2\Omega$		13		ns
t _f	Fall Time			6.3		ns
Diode C	haracteristics	· · · · · · · · · · · · · · · · · · ·				
V _{SD}	Diode Forward Voltage	$I_{S} = 24A, V_{GS} = 0V$		0.85	1	V
Q _{rr}	Reverse Recovery Charge	V _{DD} = 12.5V, I _F = 24A, di/dt = 300A/µs		21		nC
t _{rr}	Reverse Recovery Time	V _{DD} = 12.5V, I _F = 24A, di/dt = 300A/µs		16		ns



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THERMAL INFORMATION

	THERMAL METRIC ⁽¹⁾⁽²⁾	CSD16323Q3	
		8 PINS	UNITS
θ_{JA}	Junction-to-ambient thermal resistance	42.0	
θ _{JCtop}	Junction-to-case (top) thermal resistance	20.6	
θ_{JB}	Junction-to-board thermal resistance	8.8	°C/M
Ψ _{JT}	Junction-to-top characterization parameter	0.3	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	8.7	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance	0.1	

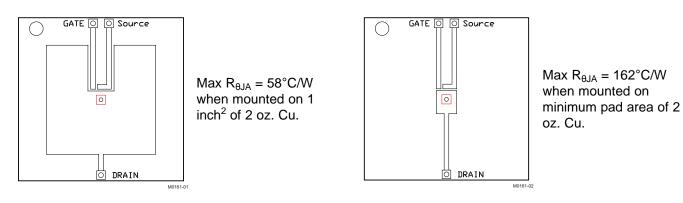
For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.
 For thermal estimates of this device based on PCB copper area, see the TI PCB Thermal Calculator.

CSD16323Q3

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TYPICAL MOSFET CHARACTERISTICS

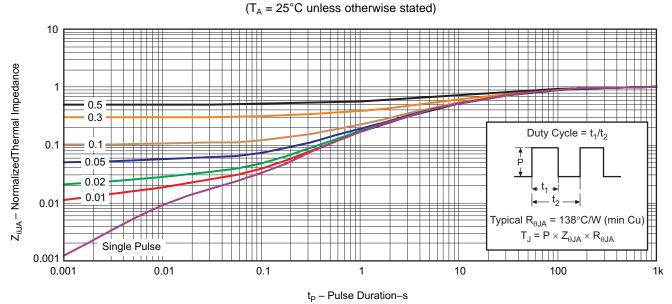


Figure 1. Transient Thermal Impedance

G012

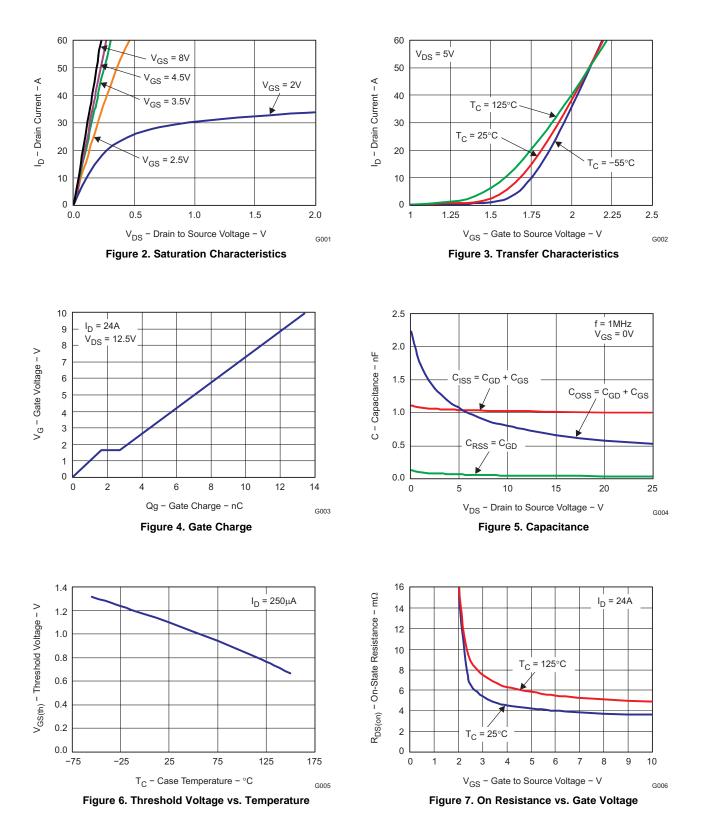


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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$



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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

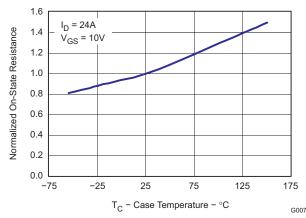


Figure 8. Normalized On Resistance vs. Temperature

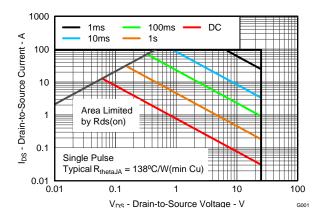


Figure 10. Maximum Safe Operating Area

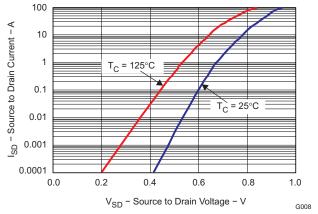


Figure 9. Typical Diode Forward Voltage

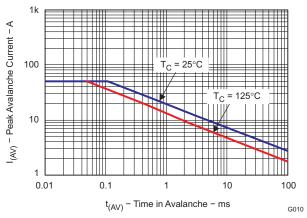
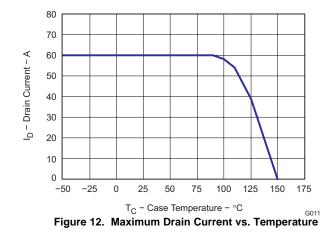


Figure 11. Single Pulse Unclamped Inductive Switching

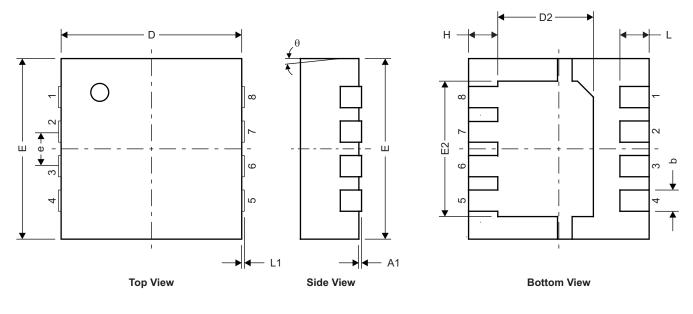


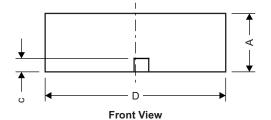


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MECHANICAL DATA

Q3 Package Dimensions





M0142-01

DIM		MILLIMETERS	6		INCHES	
	MIN	NOM	MAX	MIN	NOM	MAX
А	0.950	1.000	1.100	0.037	0.039	0.043
A1	0.000	0.000	0.050	0.000	0.000	0.002
b	0.280	0.340	0.400	0.011	0.013	0.016
С	0.150	0.200	0.250	0.006	0.008	0.010
D	3.200	3.300	3.400	0.126	0.130	0.134
D1	-	_	-	_	_	-
D2	1.650	1.750	1.800	0.065	0.069	0.071
Е	3.200	3.300	3.400	0.126	0.130	0.134
E1	-	_	_	_	_	-
E2	2.350	2.450	2.550	0.093	0.096	0.100
е		0.650 TYP			0.026	
Н	0.35	0.450	0.550	0.014	0.018	0.022
L	0.35	0.450	0.550	0.014	0.018	0.022
L1	-	_	_	_	_	-
θ	_	_	_	_	_	-

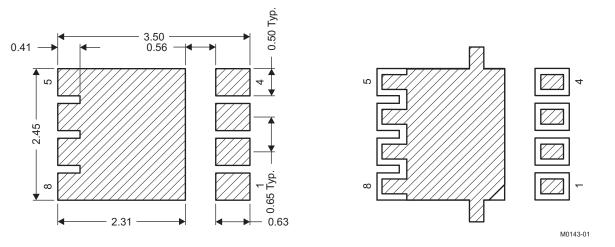
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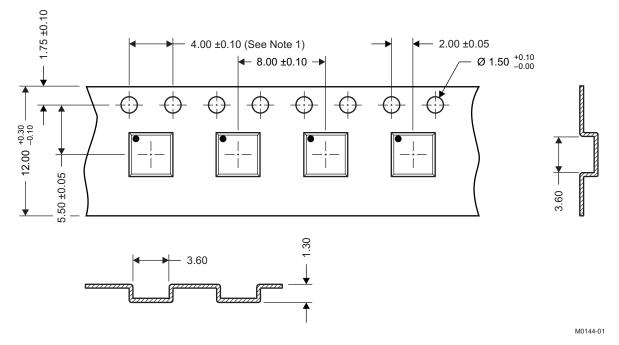
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Recommended PCB Pattern



For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q3 Tape and Reel Information



Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ± 0.2
- 2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. Thickness: 0.30 ±0.05mm
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible



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REVISION HISTORY

Changes from Original (August 2009) to Revision A	Page
- Changed $R_{DS(on)}$ - V_{GS} = 3V, I_D = 24A MAX value From: 6.5 To: 7.2	
Deleted the Package Marking Information section	
Changes from Revision A (April 2010) to Revision B	Page
 Changes from Revision A (April 2010) to Revision B Replaced the THERMAL CHARACTERISTICS table with the new Thermal Information Table Replaced Figure 10 - Maximum Safe Operating Area 	

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	-	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16323Q3	SON	DQG	8	2500	330.0	12.8	3.6	3.6	1.2	8.0	12.0	Q1

TEXAS INSTRUMENTS

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PACKAGE MATERIALS INFORMATION

1-Aug-2013



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD16323Q3	SON	DQG	8	2500	335.0	335.0	32.0

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